CAN SHENG CS®

深圳灿升实业发展有限公司

TRANSISTOR PNP

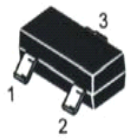
A1015

SOT-23 Plastic-Encapsulate Transistors

FEATURES

- High voltage and high current
  VCEO:=-50V(min.),IC=-150mA(max.)
- Excellent hFE Linearity
  hFE (2)=80(Typ.) at VCE=-6V,IC=-150mA
  hFE (IC=-0.1mA)/hFE(IC=-2mA)=0.95(Typ.)
- Low niose :NF=1dB(Typ)atf=1KHZ
- Complementary to C1815

SOT-23



1、BASE
2、EMITTER
3、COLLECTOR

MARKING: BA

MAXIMUM RATINGS (TA=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	-50	V
VCEO	Collector-Emitter Voltage	-50	V
VEBO	Emitter-Base Voltage	-5	V
IC	Collector Current -Continuous	150	mA
PC	Collector Power Dissipation	200	mW
TJ	Junction Temperature	125	℃
Tstg	Storage Temperature	-55-125	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC= -100u A, IE=0	-50			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= -0.1mA, IB=0	-50			V
Emitter-base breakdown voltage	V(BR)EBO	IE= -100 u A, IC=0	-5			V
Collector cut-off current	ICBO	VCB=-50V , IE=0			-0.1	u A
Collector cut-off current	ICEO	VCE= -50V , IB=0			-0.1	u A
Emitter cut-off current	IEBO	VEB=- 5V, IC=0			-0.1	u A
DC current gain	hFE	VCE=-6V, IC= -2mA	130		400	
Collector-emitter saturation voltage	VCE(sat)	IC=-100 mA, IB= -10mA			-0.3	V
Base-emitter saturation voltage	VBE(sat)	IC=-100 mA, IB= -10mA			-1.1	V
Transition frequency	fT	VCE=-10V, IC= -1mA f=30MHz	80			MHz

CLASSIFICATION OF h_{FE}

Rank	L	H
Range	130-200	200-400

Typical Characteristics A1015